

Page i

DIODES, SILICON, POWER RECTIFIER,

FAST RECOVERY,

BASED ON TYPES 1N5415 THROUGH 1N5420

ESCC Detail Specification No. 5103/007

ISSUE 1 October 2002



Document Custodian: European Space Agency - see https://escies.org



LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2002. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Ageny and provided that it is not used for a commercial purpose, may be:

- copied in whole in any medium without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



european space agency agence spatiale européenne

Pages 1 to 19

DIODES, SILICON, POWER RECTIFIER,

FAST RECOVERY,

BASED ON TYPES 1N5415 THROUGH 1N5420

ESA/SCC Detail Specification No. 5103/007

space components coordination group

		Appr	Approved by			
Issue/Rev.	Date	SCCG Chairman	ESA Director General or his Deputy			
Issue 1	August 1985	-	-			
Revision 'A'	October 1985	-				
Revision 'B'	July 1993	Tomments	I lut			
Revision 'C'	July 1996	Sa mitt	Aom			



Rev. 'C'

PAGE 2

DOCUMENTATION CHANGE NOTICE

Rev. Letter	Rev. Date	CHANGE Reference Item	Approved DCR No.
'A'	Oct. '85	P1. Cover page P2. DCN P6. Table 1(a) : Type identification in Column 2 corrected	None None 23222
'Β'	July '93	 P1. Cover Page P2. DCN P9. Para. 4.2.2 : PIND deviation amended P10. Para. 2 : MIL-STD-1276 deleted Para. 4.2.3 : Radiographic Inspection deviation amended P15. Table 3 : Note 1 deleted, subsequent note renumbered 	None 21043 21025 21049 21047
,C,	July '96	P1. Cover page P2. DCN P5. Para. 1.7 : Text amended P6. Table 1(a) : Lead finish corrected P11. Para. 4.4.2 : Text corrected	None 21083 23822 23822



No. 5103/007

TABLE OF CONTENTS

1.	GENERAL	Page 5
1.1	Scope	5
1.2	Component Type Variants	5
1.3	Maximum Ratings	5
1.4	Parameter Derating Information	5
1.5	Physical Dimensions	5
1.6	Functional Diagram	5
1.7	High Temperature Test Precautions	5
2.	APPLICABLE DOCUMENTS	9
3.	TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS	9
4.	REQUIREMENTS	9
4.1	General	9
4.2	Deviations from Generic Specification	9
4.2.1	Deviations from Special In-process Controls	9
4.2.2	Deviations from Final Production Tests (Chart II)	9
4.2.3	Deviations from Burn-in and Electrical Measurements (Chart III)	10
4.2.4	Deviations from Qualification Tests (Chart IV)	10
4.2.5	Deviations from Lot Acceptance Tests (Chart V)	10
4.3	Mechanical Requirements	10
4.3.1	Dimension Check	10
4.3.2	Weight	10
4.3.3	Terminal Strength	10
4.4	Materials and Finishes	11
4.4.1 4.4.2	Case Lead Material and Finish	11
4.4.∠ 4.5		11 11
4.5 4.5.1	Marking General	11
4.5.1	Lead Identification	11
4.5.2	The SCC Component Number	11
4.5.3	Traceability Information	12
4.5.4 4.5.5	Marking of Small Components	12
4.5.5 4.6	Electrical Measurements	12
4.6.1	Electrical Measurements at Room Temperature	12
4.6.2	Electrical Measurements at High and Low Temperatures	12
4.6.3	Circuits for Electrical Measurements	12
-T.U.U		12

Bee	ESA/SCC Detail Specification No. 5103/007		PAGË ISSUE	4 1
------------	--	--	---------------	--------

		Page
4.7	Burn-in Tests	13
4.7.1	Parameter Drift Values	13
4.7.2	Conditions for Burn-in	13
4.7.3	Electrical Circuits for Burn-in	13
4.8	Environmental and Endurance Tests	18
4.8.1	Electrical Measurements on Completion of Environmental Tests	18
4.8.2	Electrical Measurements at Intermediate Points during Endurance Tests	18
4.8.3	Electrical Measurements on Completion of Endurance Tests	18
4.8.4	Conditions for Operating Life Tests (Part of Endurance Testing)	18
4.8.5	Electrical Circuits for Operating Life Tests	18
4.8.6	Conditions for High Temperature Storage Test (Part of Endurance Testing)	18
TABLE	<u>'S</u>	
1(a)	Type Variants	6
1(b)	Maximum Ratings	6
2	Electrical Measurements at Room Temperature - d.c. parameters	14
	Electrical Measurements at Room Temperature - a.c. parameters	14
3	Electrical Measurements at High and Low Temperatures	15
4	Parameter Drift Values	15
5	Conditions for Burn-in and Operating Life Tests	17

6 Electrical Measurements at Intermediate Points and on Completion of Endurance Testing 19

FIGURES

1	Parameter Derating Information	7
2	Physical Dimensions	8
3	Functional Diagram	8
4	Circuit for Electrical Measurements - Reverse Recovery Time	16

APPENDICES (Applicable to specific Manufacturers only) None.



PAGE

5

1

1. <u>GENERAL</u>

1.1 <u>SCO</u>PE

This specification details the ratings, physical and electrical characteristics, test and inspection data for Diodes, Silicon, Power Rectifier, Fast Recovery, based on Types 1N5415 through 1N5420.

It shall be read in conjunction with ESA/SCC Generic Specification No. 5000, the requirements of which are supplemented herein.

1.2 COMPONENT TYPE VARIANTS

Variants of the basic diodes specified herein, which are also covered by this specification, are listed in Table 1(a).

1.3 MAXIMUM RATINGS

The maximum ratings, which shall not be exceeded at any time during use or storage, applicable to the diodes specified herein, are scheduled in Table 1(b).

1.4 PARAMETER DERATING INFORMATION

The derating information applicable to the diodes specified herein is shown in Figure 1.

1.5 PHYSICAL DIMENSIONS

The physical dimensions of the diodes specified herein are shown in Figure 2.

1.6 FUNCTIONAL DIAGRAM

The functional diagram, showing lead identification, of the diodes specified herein, is shown in Figure 3.

1.7 HIGH TEMPERATURE TEST PRECAUTIONS

For tin-lead plated or solder-dipped lead finish, all tests to be performed at a temperature that exceeds +125°C shall be carried out in a 100% inert atmosphere.



6

PAGE

TABLE 1(a) - COMPONENT TYPE VARIANTS

(1)	(2)	(3)	(4)	(5)	(6)	(7)
VARIANT	TYPE	REVERSE VOLTAGE	BREAKDOWN VOLTAGE	JUNCTION CAPACITANCE	REVERSE RECOVERY TIME	Lead Material and Finish
		(V)	(V)	(pF)	(ns)	
01	1N5415	50	55	550	150	A10
02	1N5415	50	55	550	150	A3 or A4
03	1N5416	100	110	430	150	A10
04	1N5416	100	110	430	150	A3 or A4
05	1N5417	200	220	250	150	A10
06	1N5417	200	220	250	150	A3 or A4
07	1N5418	400	440	165	150	A10
08	1N5418	400	440	165	150	A3 or A4
09	1N5419	500	550	140	250	A10
10	1N5419	500	550	140	250	A3 or A4
11	1N5420	600	660	120	400	A10
12	1N5420	600	660	120	400	A3 or A4

TABLE 1(b) - MAXIMUM RATINGS

No.	CHARACTERISTIC	SYMBOL	MAXIMUM RATING	UNIT	NOTES
1	Forward Surge Current	I _{FSM}	80	А	1
2	Reverse Voltage	V _R	See Note 2	V	
3	Average Output Rectified Current	lo	3.0	А	3
4	Operating Temperature Range	T _{op}	65 to +175	°C	T _{amb}
5	Storage Temperature Range	T _{stg}	- 65 to + 200	°C	
6	Soldering Temperature	T _{sol}	+ 245	°C	4

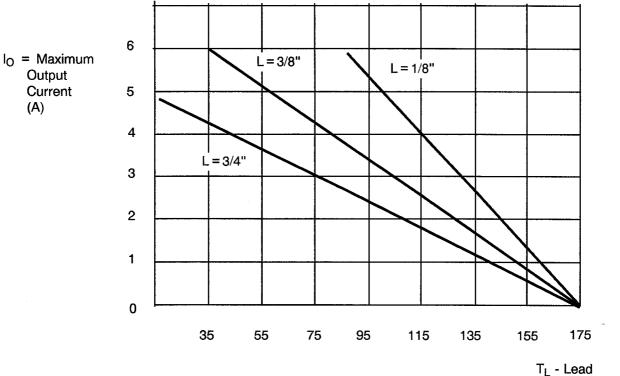
NOTES

- 1. Sinusoidal, with period = 8.3ms maximum.2. See Column 3 of Table 1(a).3. At T_{amb} = \leq + 55°C. For derating of I_O with T_L, see Figure 1.
- 4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the can and the same lead shall not be resoldered until 3 minutes have elapsed.



7

FIGURE 1 - PARAMETER DERATING INFORMATION



Temperature(°C)

NOTES

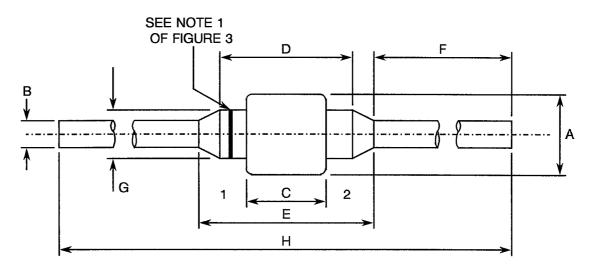
1. L = Lead length from body in inches.

Output Current Derating with Lead Temperature for Different Lead Lengths



No. 5103/007

FIGURE 2 - PHYSICAL DIMENSIONS

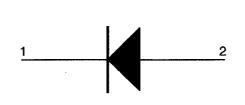


SYMBOL	INC	HES	MILLIMETRES		
STMBOL	MIN.	MAX.	MIN.	MAX.	
А	-	0.145	-	3.7	
В	0.039	0.041	0.99	1.04	
С	-	0.110	-	2.8	
D	-	0.180	-	4.6	
Е	-	0.300	-	7.6	
F	0.975	-	24.8	-	
G	-	0.120	-	3.0	
Н	2.300	-	58.4	-	

FIGURE 3 - FUNCTIONAL DIAGRAM

1. Cathode

2. Anode





1. The cathode end shall be marked with a coloured ring.



2. APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:-

- (a) ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors.
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices.

3. TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESA/SCC Basic Specification No. 21300 shall apply.

4. REQUIREMENTS

4.1 GENERAL

The complete requirements for procurement of the diodes specified herein are stated in this specification and ESA/SCC Generic Specification No. 5000 for Discrete Semiconductors. Deviations from the Generic Specification applicable to this specification only, are listed in Para. 4.2.

Deviations from the applicable Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESA/SCC requirements and do not affect the components' reliability, are listed in the appendices attached to this specification.

4.2 **DEVIATIONS FROM GENERIC SPECIFICATION**

4.2.1 Deviations from Special In-process Controls None.

4.2.2 Deviations from Final Production Tests (Chart II)

- (a) Bond Strength Test: Shall not be performed.
- (b) Die-shear Test: Shall not be performed.
- (c) Para. 9.7, Particle Impact Noise Detection (PIND) Test: Not applicable.
- (d) The following test shall be added after Para. 9.8.2, Seal Test, Fine and Gross Leak (Optional) and before Para. 9.9.3, Electrical Measurements at Room Temperature:-

Rev. 'B'

Surge current in accordance with Test method 4066 of MIL-STD-750. The following test conditions shall apply:-

 $\begin{array}{lll} T_{amb} & : & \pm 25 \pm 3 \ ^\circ C. \\ I_{FSM} & : & 80A. \\ Number of pulses & : & 5. \\ Pulse rate & : & 1 \ pulse/minute. \\ t_p & : & 8.3ms. \\ Pulse form & : & sinusoidal. \end{array}$

ste

4.2.3 Deviations from Burn-in and Electrical Measurements (Chart III)

- (a) High Temperature Reverse Bias: Shall not be performed.
- (b) Para. 9.12, Radiographic Inspection: Not applicable.

4.2.4 Deviations from Qualification Tests (Chart IV)

- (a) Bond Strength Test: Shall not be performed.
- (b) Die-shear Test: Shall not be performed.
- 4.2.5 Deviations from Lot Acceptance Tests (Chart V) None.
- 4.3 MECHANICAL REQUIREMENTS

4.3.1 Dimension Check

The dimensions of the diodes specified herein shall be checked. They shall conform to those shown in Figure 2.

4.3.2 Weight

The maximum weight of the diodes specified herein shall be 0.25 grammes.

4.3.3 Terminal Strength

The requirements for terminal strength testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The test conditions shall be as follows:-

Test Condition :'A'.Applied Force :22.2 Newtons.Duration :15 seconds.



PAGE 11

MATERIALS AND FINISHES 4.4

The materials and finishes shall be as specified herein. Where a definite material is not specified, a material which will enable the diodes specified herein to meet the performance requirements of this specification shall be used. Acceptance or approval of any constituent material does not guarantee acceptance of the finished product.

4.4.1 Case

Glass, hermetically sealed.

4.4.2 Lead Material and Finish

The lead material shall be Type 'A' with either Type '3 or 4' or Type '10' finish in accordance with the requirements of ESA/SCC Basic Specification No. 23500. (See Table 1(a) for Type Variants).

4.5 MARKING

4.5.1 General

The marking of all components delivered to this specification shall be in accordance with the requirements of ESA/SCC Basic Specification No. 21700. Each component shall be marked in respect of:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

4.5.2 Lead Identification

Lead identification shall be as shown in Figures 2 and 3.

4.5.3 The SCC Component Number

Each component shall bear the SCC Component Number which shall be constituted and marked as follows:

Detail Specification Number	<u>510300702</u> B
Type Variant	
Testing Level (B or C, as applicable)	



4.5.4 Traceability Information

Each component shall be marked in respect of traceability information in accordance with the requirements of ESA/SCC Basic Specification No. 21700.

4.5.5 Marking of Small Components

When it is considered that the component is too small to accommodate the marking as specified above, as much as space permits shall be marked. The order of precedence shall be as follows:-

- (a) Lead Identification.
- (b) The SCC Component Number.
- (c) Traceability Information.

The marking information in full shall accompany each component in its primary package.

4.6 ELECTRICAL CHARACTERISTICS

4.6.1 <u>Electrical Measurements at Room Temperature</u>

The parameters to be measured at room temperature are scheduled in Table 2. The measurements shall be performed at T_{amb} = +22 ± 3 °C.

4.6.2 <u>Electrical Measurements at High and Low Temperatures</u>

The parameters to be measured at high and low temperatures are scheduled in Table 3.

4.6.3 <u>Circuits for Electrical Measurements</u>

Circuits for use in performing the electrical measurements listed in Tables 2 and 3 of this specification are shown, where applicable, in MIL-STD-750 and Figure 4.



4.7 BURN-IN TESTS

4.7.1 Parameter Drift Values

The parameter drift values applicable to burn-in are specified in Table 4 of this specification. Unless otherwise stated, the measurements shall be performed at $T_{amb} = +22 \pm 3$ °C. The parameter drift values (Δ) applicable to the parameters scheduled, shall not be exceeded. In addition to these drift value requirements, the appropriate limit value specified for a given parameter in Table 2 shall not be exceeded.

4.7.2 Conditions for Burn-in

The requirements for burn-in are specified in Section 7 of ESA/SCC Generic Specification No. 5000. The conditions for burn-in shall be as specified in Table 5 of this specification.

4.7.3 <u>Electrical Circuits for Burn-in (Figure 5)</u>

Not applicable.



TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - d.c. PARAMETERS

No.	CHARACTERISTICS	SYMBOL	TEST METHOD	DD TEST CONDITION	LIM	UNIT	
INO.		OTMDOL	MIL-STD-750		MIN.	MAX.	UNIT
1	Reverse Current	I _R	4016	V _R = (1) V	-	1.0	μA
2	Forward Voltage	V _F	4011	l _F = 9.0A See Note 2	0.6	1.5	V
3	Breakdown Voltage	V _(BR)	4021	l _R = 50μA	(3)	-	V

TABLE 2 - ELECTRICAL MEASUREMENTS AT ROOM TEMPERATURE - a.c. PARAMETERS

No.	CHARACTERISTICS	HARACTERISTICS SYMBOL	TEST METHOD	TEST CONDITION	LIMITS		UNIT
140.	UNA DOTENIO 100	OTWDOL	MIL-STD-750	(Note 6)	MIN.	MAX.	UNIT
4	Junction Capacitance	CJ	4001	V _R = 4.0V f = 1.0MHz	-	(4)	pF
5	Reverse Recovery Time	t _{rr}	4031	I _F = 0.5A I _R = 1.0A I _{RR} = 0.25A (See Figure 4)	-	(5)	ns

NOTES

- 1. See Column 3 of Table 1(a).
- 2. Pulse Measurement with tp = 300μ s; Duty Cycle $\leq 2\%$.
- 3. See Column 4 of Table 1(a).
- 4. See Column 5 of Table 1(a).
- 5. See Column 6 of Table 1(a).
- 6. A.C. parameters shall be performed on a sample basis LTPD = 7, or less (see Annex 1 of ESA/SCC Generic Specification No. 5000).



Rev. 'B'

TABLE 3 - ELECTRICAL MEASUREMENTS AT HIGH AND LOW TEMPERATURES

No.	CHARACTERISTICS	SYMBOL	TEST METHOD MIL-STD-750	TEST CONDITIONS	LIMI MIN.	ITS	UNIT
				TEST CONDITIONS		MAX.	
1	Reverse Current	l _R	4016	V _R = (1) T _{amb} = + 100 (+0-5) °C	-	20	μΑ

<u>NOTES</u>

1. See Column 3 of Table 1(a).

TABLE 4 - PARAMETER DRIFT VALUES

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITION	CHANGE LIMITS (Δ)	UNIT
1	Reverse Current	l _R	As per Table 2	As per Table 2	±0.25 or (1) ±100	µА %
2	Forward Voltage	V _F	As per Table 2	As per Table 2	± 100	mV

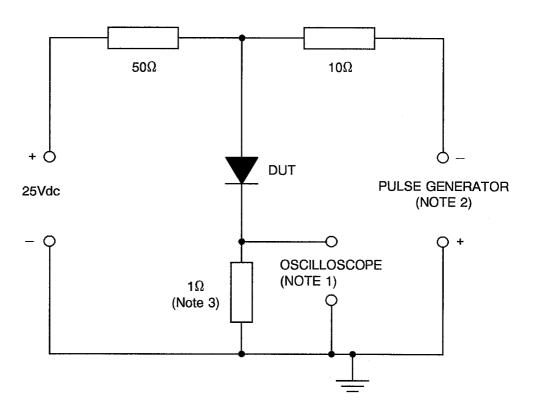
NOTES

1. Whichever is the greater referred to the initial value.



FIGURE 4 - CIRCUITS FOR ELECTRICAL MEASUREMENTS

REVERSE RECOVERY TIME



NOTES

- 1. Oscilloscope: $t_r \le 3.0$ ns; $Z_{IN} = 50\Omega$.2. Pulse Generator: $t_r \le 8.0$ ns; $Z_S = 10\Omega$.
- 3. Current viewing resistor, non-inductive, coaxial.



TABLE 5 - CONDITIONS FOR BURN-IN AND OPERATING LIFE TESTS

No.	CHARACTERISTICS	SYMBOL	CONDITION	UNIT
1	Ambient Temperature	T _{amb}	+ 25 ± 3	°C
2	Peak Reverse Voltage	V _{RM}	V _{RM} = (1)	Vrms
5	Frequency	f	50 to 60	Hz
4	Average Output Rectified Current	lo	3.0 See Note 2	A

NOTES

1. See Column 3 of Table 1(a).

2. Mounting shall be performed without bending or soldering the leads. Lead length from body to mounting shall be 0.12 inches (3.14mm) minimum.



4.8 <u>ENVIRONMENTAL AND ENDURANCE TESTS (CHARTS IV AND V OF ESA/SCC GENERIC</u> SPECIFICATION No. 5000)

4.8.1 <u>Electrical Measurements on Completion of Environmental Tests</u>

The parameters to be measured on completion of environmental tests are scheduled in Table 2. The measurements shall be performed at T_{amb} = +22±3 °C.

4.8.2 <u>Electrical Measurements at Intermediate Points during Endurance Tests</u>

The parameters to be measured at intermediate points during endurance tests are scheduled in Table 6.

4.8.3 Electrical Measurements on Completion of Endurance Tests

The parameters to be measured on completion of endurance testing are scheduled in Table 6. The measurements shall be performed at Tamb = $+22 \pm 3$ °C.

4.8.4 <u>Conditions for Operating Life Tests (Part of Endurance Testing)</u>

The requirements for operating life testing are specified in Section 9 of ESA/SCC Generic Specification No. 5000. The conditions for operating life testing shall be as specified in Table 5 of this specification.

4.8.5 <u>Electrical Circuits for Operating Life Tests (Figure 5)</u> Not applicable.

4.8.6 <u>Conditions for High Temperature Storage Test (Part of Endurance Testing)</u>

The requirements for the high temperature storage test are specified in ESA/SCC Generic Specification No. 5000. The conditions for high temperature storage shall be T_{amb} = +200 (+0-5) °C.



TABLE 6 - ELECTRICAL MEASUREMENTS AT INTERMEDIATE POINTS AND ON COMPLETION OF ENDURANCE TESTING

No.	CHARACTERISTICS	SYMBOL	SPEC. AND/OR TEST METHOD	TEST CONDITION	LIMITS		UNIT
					MIN.	MAX.	
1	Reverse Current	l _R	As per Table 2	As per Table 2	-	1.0	μA
2	Forward Voltage	V _F	As per Table 2	As per Table 2	0.6	1.5	V
3	Reverse Recovery Time	t _{rr}	As per Table 2	As per Table 2	-	(1)	ns

NOTES

1. See Column 6 of Table 1(a).